

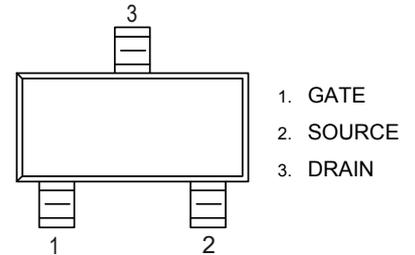
## SOT-23 Plastic-Encapsulate MOSFETS

### Feature

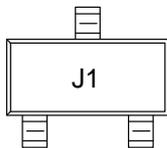
- High density cell design for extremely low  $R_{DS(on)}$
- Rugged and Reliable

### SOT-23

RoHS  
COMPLIANT

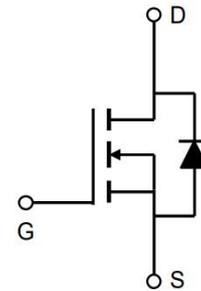


### Marking



J1 = Device code

### Equivalent Circuit



### Maximum ratings ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbo	Value	Unit
Drain-Source Voltage	$V_{DS}$	50	V
Continuous Gate-Source Voltage	$V_{GSS}$	$\pm 20$	
Continuous Drain Current	$I_D$	0.22	A
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Operating Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 ~ +150	

## Electrical characteristics (T<sub>a</sub>=25°C unless otherwise noted)

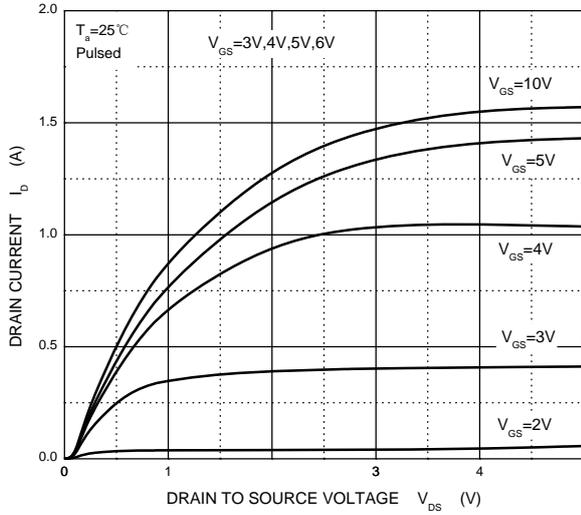
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	50			V
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V			0.5	μA
		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V			100	nA
<b>On characteristics</b>						
Gate-threshold voltage (note 1)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA	0.80		1.50	V
Static drain-source on-resistance (note 1)	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.22A			3.50	Ω
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.22A			6	
Forward transconductance (note 1)	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.22A	0.12			S
<b>Dynamic characteristics (note 2)</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		27		pF
Output capacitance	C <sub>oss</sub>			13		
Reverse transfer capacitance	C <sub>rss</sub>			6		
<b>Switching characteristics</b>						
Turn-on delay time (note 1,2)	t <sub>d(on)</sub>	V <sub>DD</sub> = 30V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.29A, R <sub>GEN</sub> = 6 Ω			5	ns
Rise time (note 1,2)	t <sub>r</sub>				18	
Turn-off delay time (note 1,2)	t <sub>d(off)</sub>				36	
Fall time (note 1,2)	t <sub>f</sub>				14	
<b>Drain-source body diode characteristics</b>						
Body diode forward voltage (note 1)	V <sub>SD</sub>	I <sub>S</sub> = 0.44A, V <sub>GS</sub> = 0V			1.4	V

**Notes:**

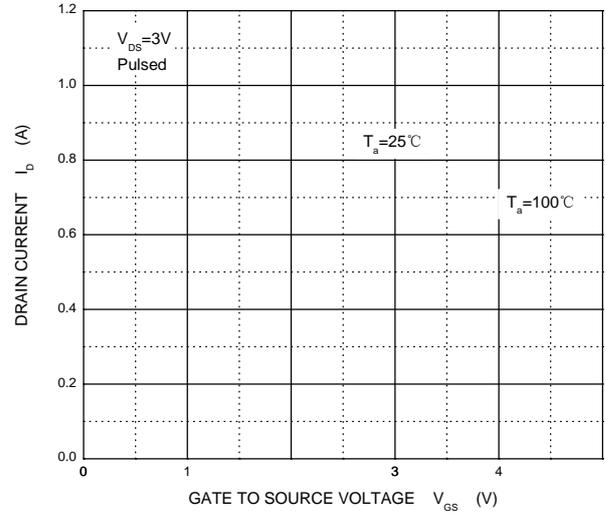
1. Pulse Test ; Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2. These parameters have no way to verify.

### Typical Characteristics

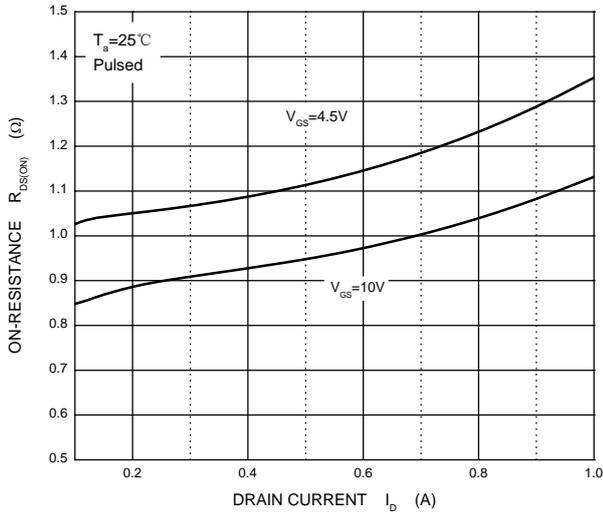
Output Characteristics



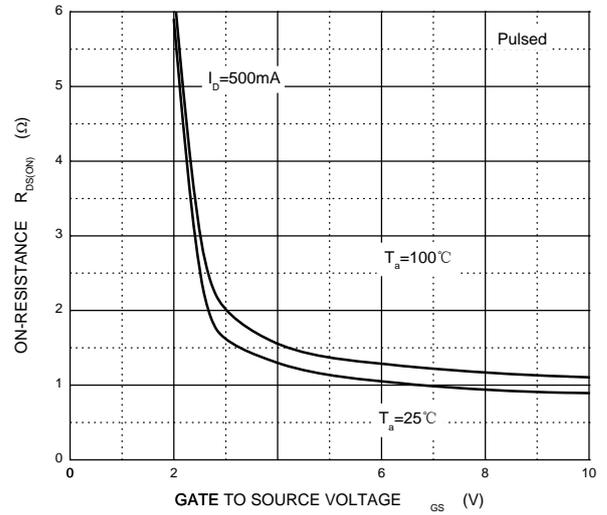
Transfer Characteristics



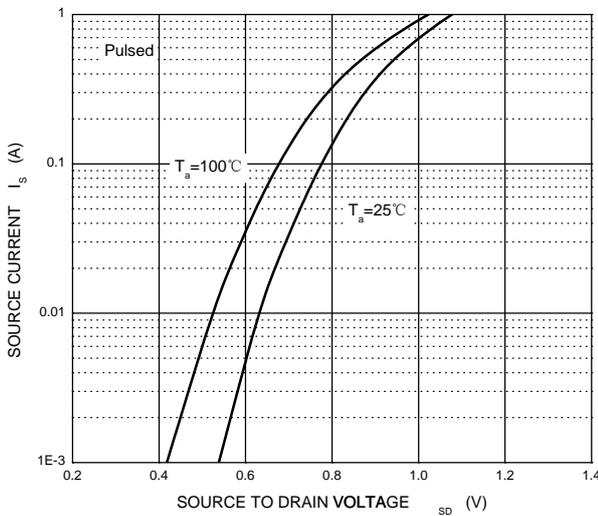
$R_{DS(ON)}$  —  $I_D$



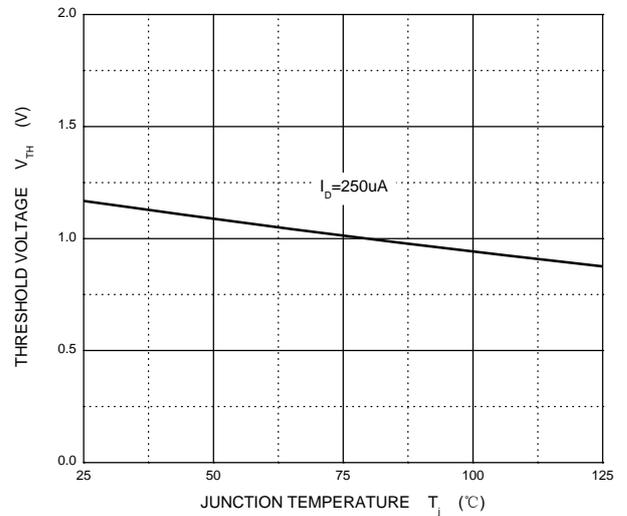
$R_{DS(ON)}$  —  $V_{GS}$



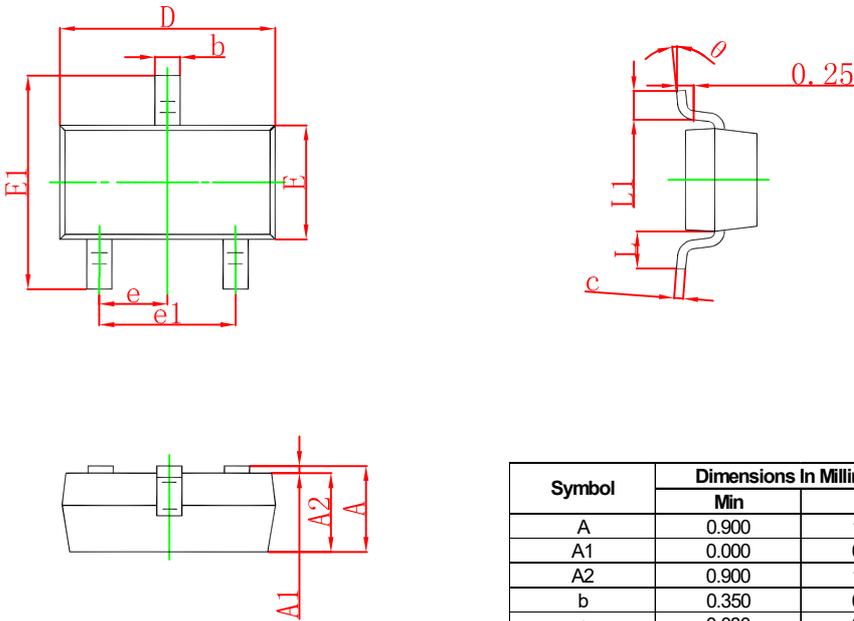
$I_S$  —  $V_{SD}$



Threshold Voltage

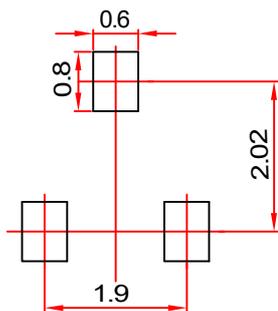


### SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.400	0.035	0.055
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.350	0.500	0.014	0.020
c	0.080	0.190	0.003	0.007
D	2.700	3.100	0.106	0.122
E	1.200	1.650	0.047	0.065
E1	2.200	3.000	0.087	0.118
e	0.950 TYP		0.037 TYP	
e1	1.780	2.040	0.070	0.080
L	0.550 REF		0.022 REF	
L1	0.200	0.500	0.008	0.020
θ	0°	8°	0°	8°

### SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in/millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.